

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A semiconductor device, comprising:
a semiconductor film;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, the gate electrode not covering any end of the semiconductor film.
2. (Previously Presented) A semiconductor device, comprising:
a semiconductor film having a source region and a drain region;
a gate insulating film formed on at least part of the semiconductor film; and
a gate electrode formed on the gate insulating film, a width of the gate electrode being smaller than a width of the semiconductor film.
3. (Previously Presented) The semiconductor device according to Claim 1, further comprising a sub gate electrode connected to the gate electrode.
4. (Previously Presented) The semiconductor device according to Claim 3, the sub gate electrode being disposed on the gate electrode.
5. (Previously Presented) The semiconductor device according to Claim 3, the sub gate electrode being disposed so as to cover at least one end of the semiconductor film.
- 6-7. (Canceled).
8. (Previously Presented) A semiconductor device, comprising:
a semiconductor film having a source region and a drain region;
a gate insulating film formed on at least part of the semiconductor film; and

a gate electrode formed on the gate insulating film, the semiconductor film including a region formed of an intrinsic semiconductor which is not doped with dopant, the region extending toward at least one of the source region and the drain region from the gate electrode.

9. (Previously Presented) A semiconductor device, comprising:

a semiconductor film having a source region and a drain region, the semiconductor film including a plurality of regions formed of an intrinsic semiconductor which is not doped with dopant;

a gate insulating film formed on at least part of the semiconductor film;

a gate electrode formed on the gate insulating film; and the regions extending toward at least one of the source region and the drain region from the gate electrode.

10. (Previously Presented) The semiconductor device according to Claim 1, the semiconductor film being formed on an insulating layer.

11. (Previously Presented) A circuit board, comprising:

the semiconductor device according to Claim 1; and

wires that supply at least one of signals and electric power to the semiconductor device.

12. (Previously Presented) An electro-optical device, comprising:

the circuit board according to Claim 11;

a first electrode formed above the circuit board; and

an electro-optical element formed above the first electrode.

13. (Currently Amended) An electro-optical device, comprising:

an electro-optical element; and

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the semiconductor device according to ~~Claim 7~~Claim 1, the electro-optical element and the semiconductor device being used as at least one electronic circuit selected from the group consisting of shift registers, level shifters, buffer circuits, and analog switches.

14. (Previously Presented) The electro-optical device according to Claim 12, the electro-optical element being an organic electroluminescence element.

15. (Previously Presented) An electronic apparatus, comprising:
the electro-optical device according to Claim 12, the electro-optical device being used as a display.
